

Amendment To The Claims:

Please cancel claims 2-11 without prejudice or disclaimer.

1. (Previously Presented) A semiconductor light-emitting device comprising:
first and second semiconductor layers each of a first conductivity type;
a third semiconductor layer of a second conductivity type provided between the first and second semiconductor layers;
an active layer provided between the second and third semiconductor layers, the active layer emitting light with charge injected therein from the second and third semiconductor layers;
and
a graded composition layer provided between the active layer and the third semiconductor layer to have a varying composition,
wherein the composition of the graded composition layer is equal to a composition of the third semiconductor layer at an interface with the third semiconductor layer, and to a composition of the active layer at an interface with the active layer,
wherein a base electrode is electrically connected to the third semiconductor layer via the graded composition layer and the active layer, and
wherein the forbidden band of the active layer is smaller than the forbidden band of the third semiconductor layer.

Claims 2-11 (Cancelled)

12. (Previously Presented) The semiconductor light-emitting device of claim 1, wherein the composition at the grade composition layer varies continuously.

13. (Previously Presented) The semiconductor light-emitting device of claim 1, wherein the composition at the grade composition layer varies stepwise.

14. (Currently Amended) The semiconductor light-emitting device of claim 1 further ~~comprises~~ comprising a base electrode interposed between the grade composition layer and the active layer, and electrically connected to the third semiconductor layer.

Claim 14 (Cancelled)

15. (Previously Presented) The semiconductor light-emitting device of claim 14, wherein regions of the active layer and the graded composition layer lying between the base electrode and the second semiconductor layer are removed.

16. (Previously Presented) The semiconductor light-emitting device of claim 1, wherein during a light-emitting period, a forward bias voltage is applied between the third semiconductor layer and the second semiconductor layer, and the potential between the third semiconductor layer and the first semiconductor layer is adjusted to 0.

17. (Previously Presented) The semiconductor light-emitting device of claim 1, wherein during an extinction period, a reverse bias voltage is applied between the third semiconductor layer and the first semiconductor layer.

18. (Previously Presented) The semiconductor light-emitting device of claim 1, wherein the third semiconductor layer is n-type.

19. (Currently Amended) The semiconductor light-emitting device of claim 1, wherein the third semiconductor layer is ~~device of~~ p-type.

20 (Previously Presented) The semiconductor light-emitting device of claim 1, wherein the third semiconductor layer is p-type.

21. (Currently Amended) The semiconductor light-emitting device of claim 20, wherein a high-resistance region is provided in a region that is opposed to the base electrode in the second semiconductor layer but not opposed to the first semiconductor layer.

22. (Previously Presented) The semiconductor light-emitting device of claim 21, wherein the high-resistance region is formed by ion implantation.